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(54) METHOD OF FORMING A SOURCE/DRAIN

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(57)**ABSTRACT**

Embodiments provide a way of treating source/drain recesses with a high heat treatment and an optional hydrogen plasma treatment. The high heat treatment smooths the surfaces inside the recesses and remove oxides and etching byproducts. The hydrogen plasma treatment enlarges the recesses vertically and horizontally and inhibits further oxidation of the surfaces in the recesses.

